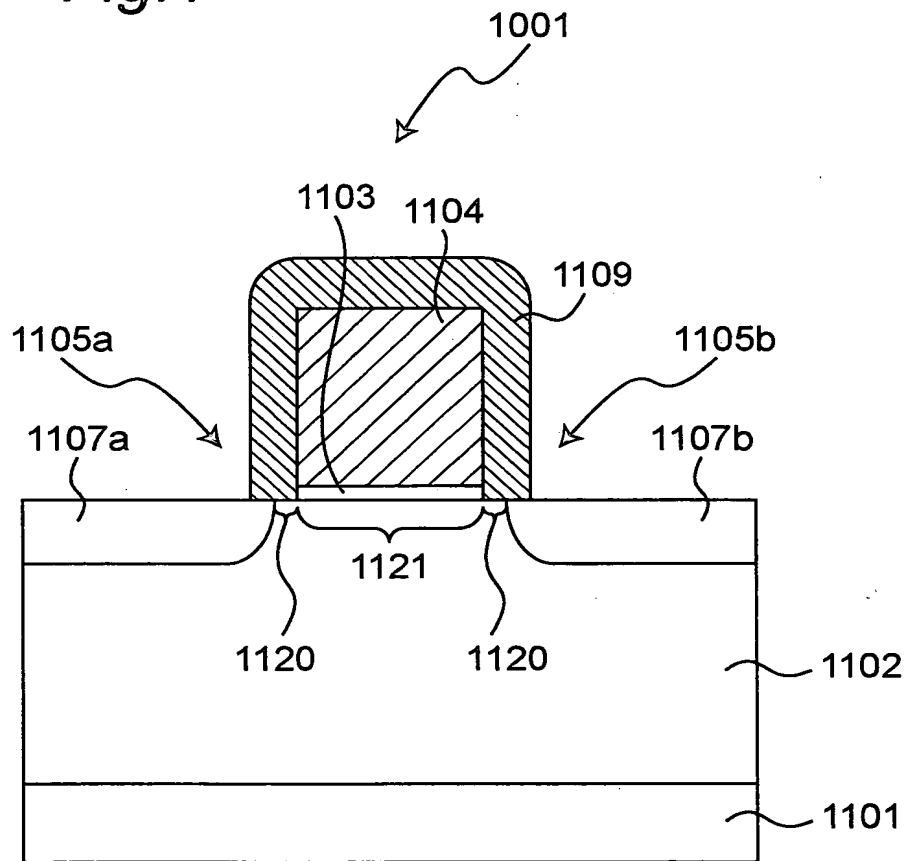


*Fig. 1*



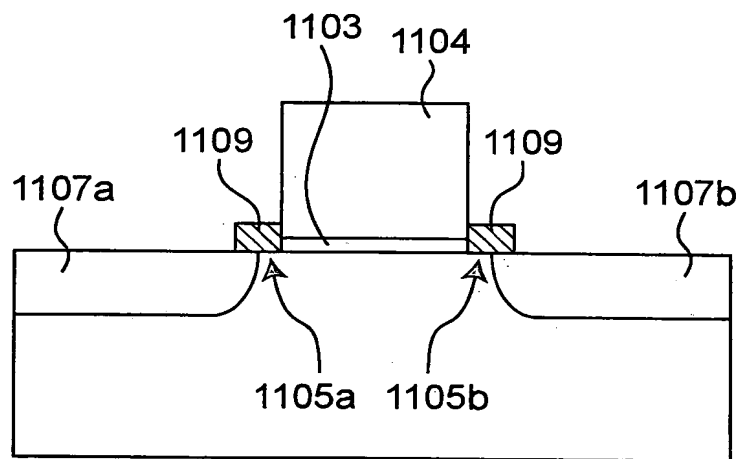
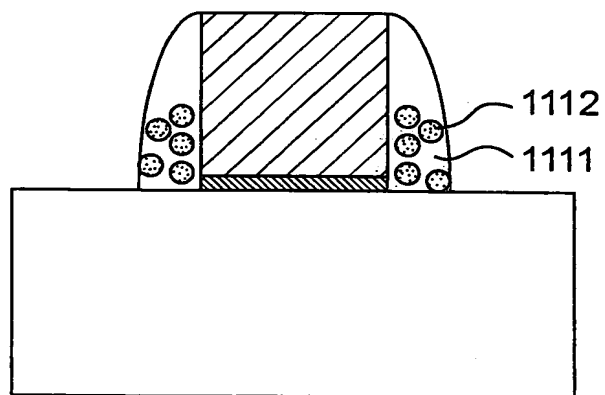
*Fig. 2A**Fig. 2B*

Fig. 3

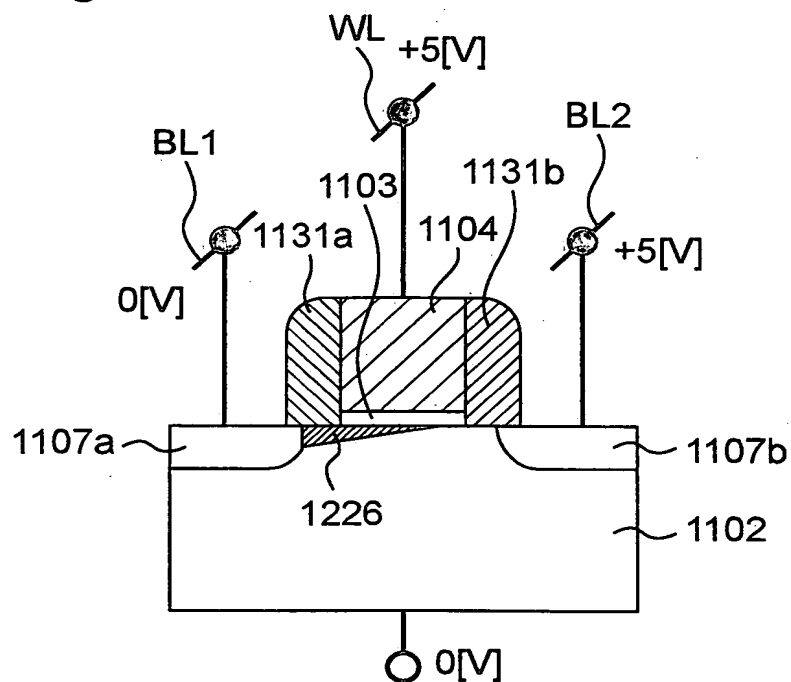


Fig. 4

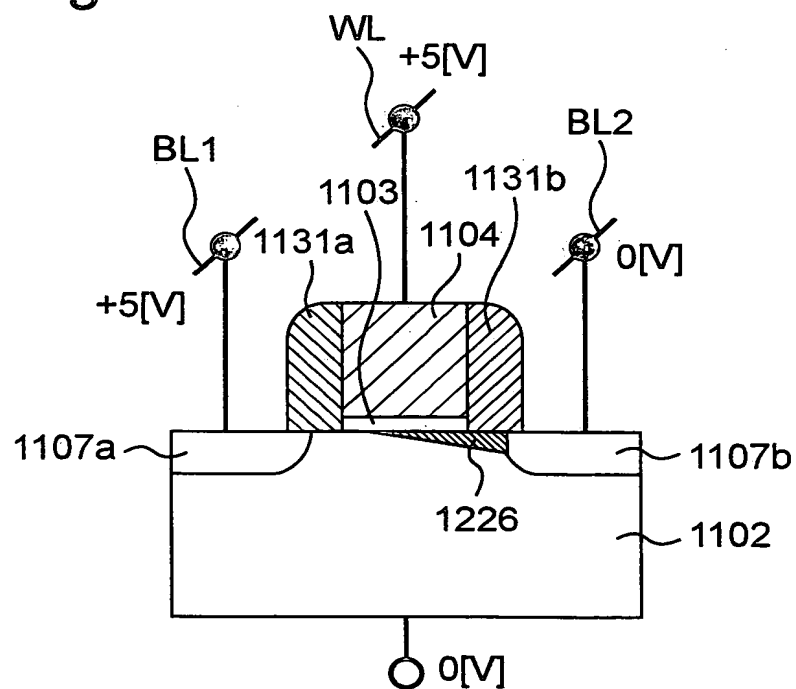


Fig. 5

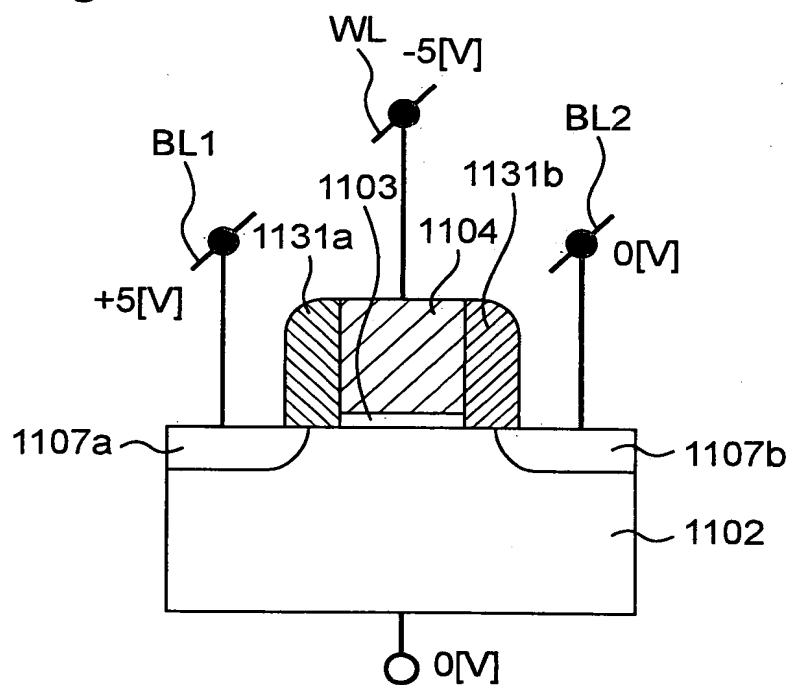


Fig. 6

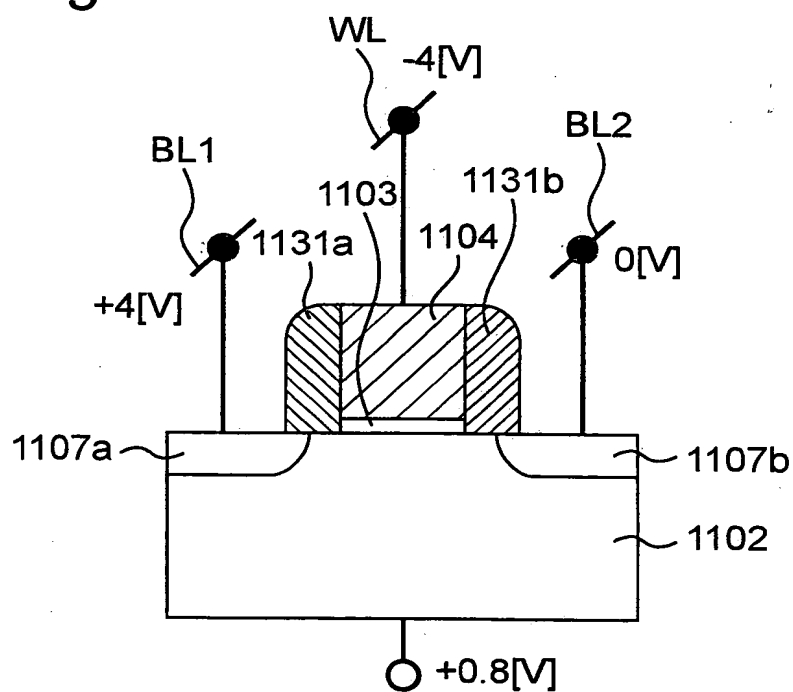


Fig. 7

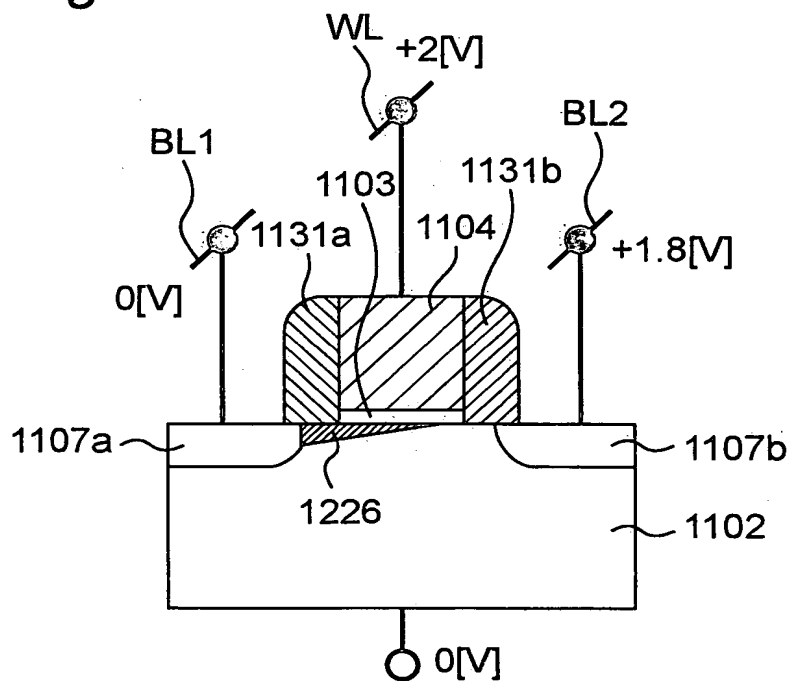


Fig. 8

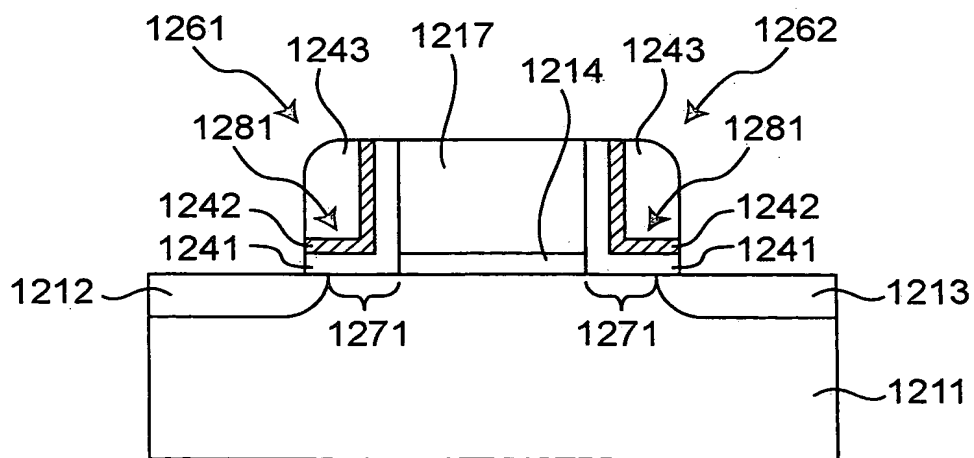


Fig. 9

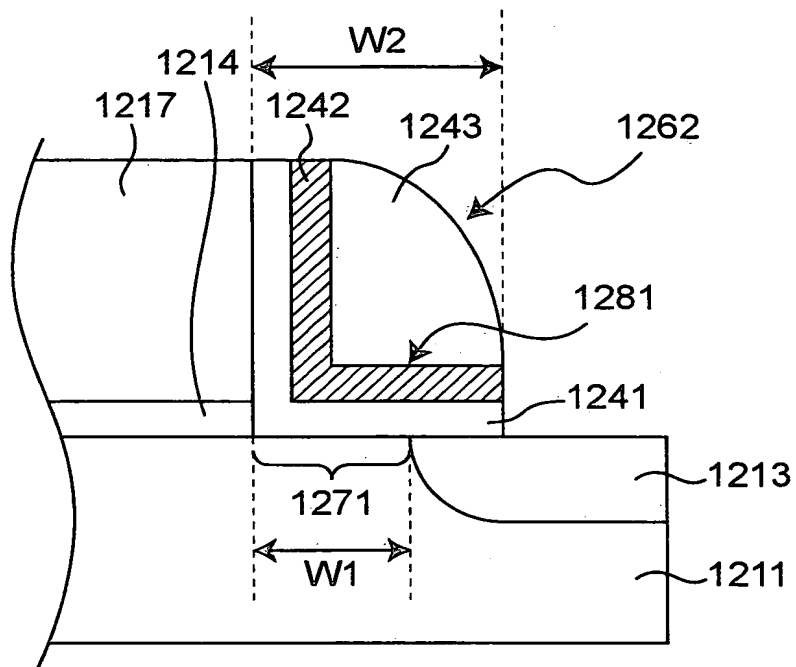


Fig. 10

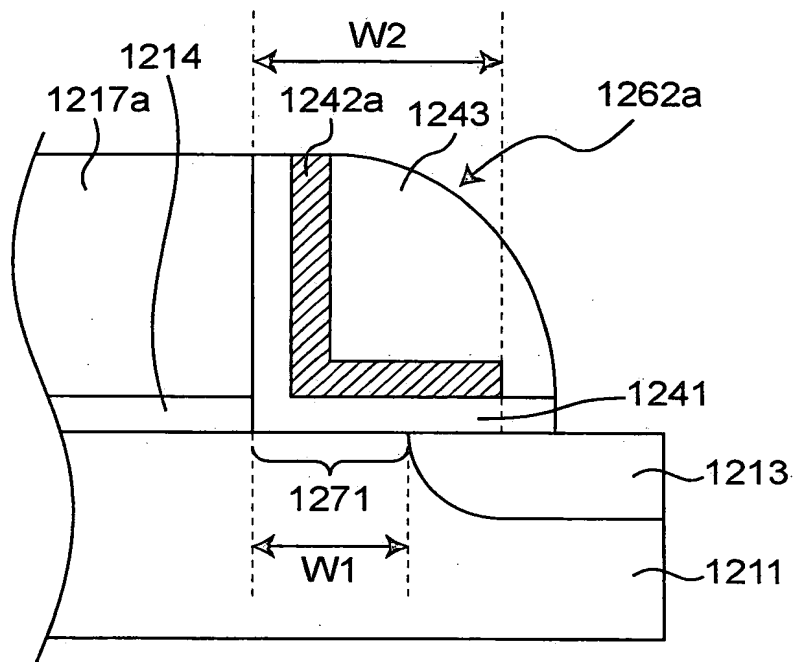


Fig. 11

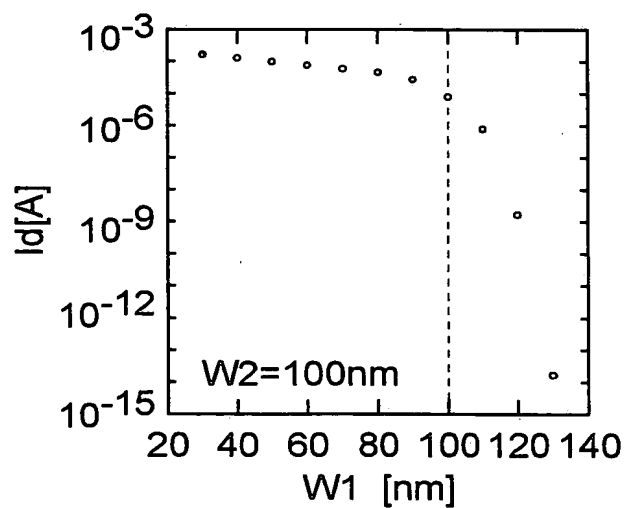


Fig. 12

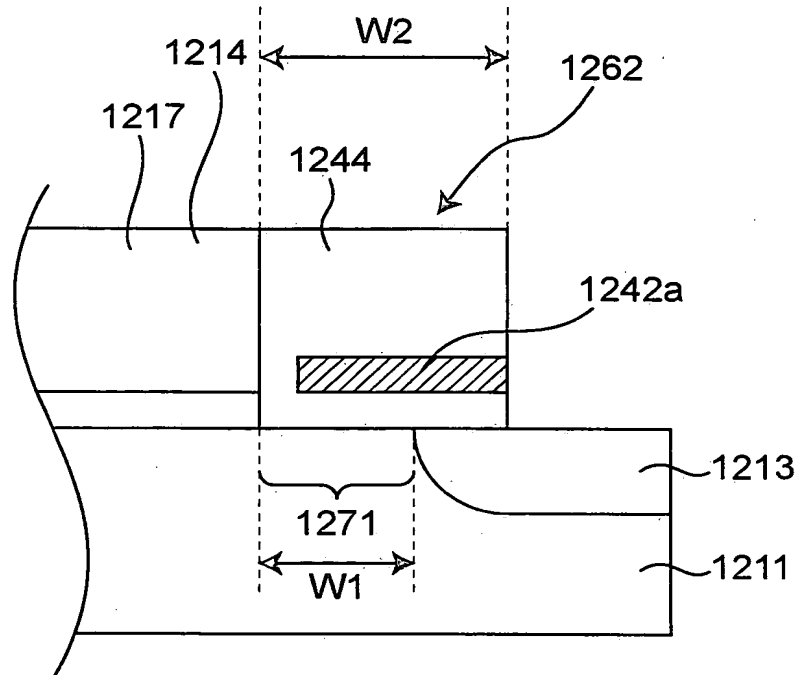
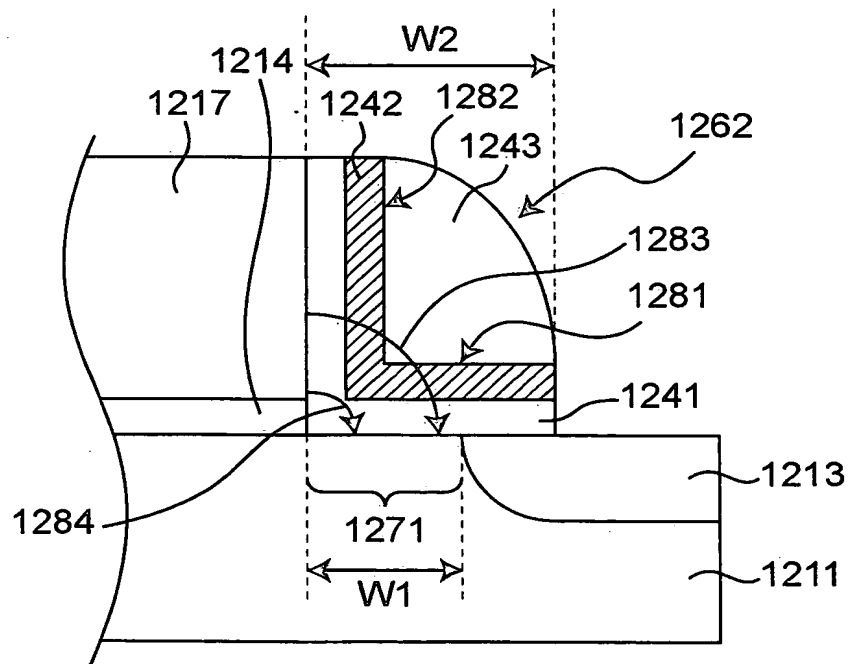


Fig. 13





[illegible]

A cross-sectional view of a semiconductor device. A central channel region 1214 is flanked by two side regions 1212 and 1213. The side regions 1212 and 1213 are further divided into sub-regions 1288, 1287, and 1286. The top surface of the device is labeled 1261 and 1262. The bottom surface is labeled 1241 and 1242. The side walls are labeled 1243. The central channel region 1214 is shown with a different hatching pattern than the side regions.



Fig. 16

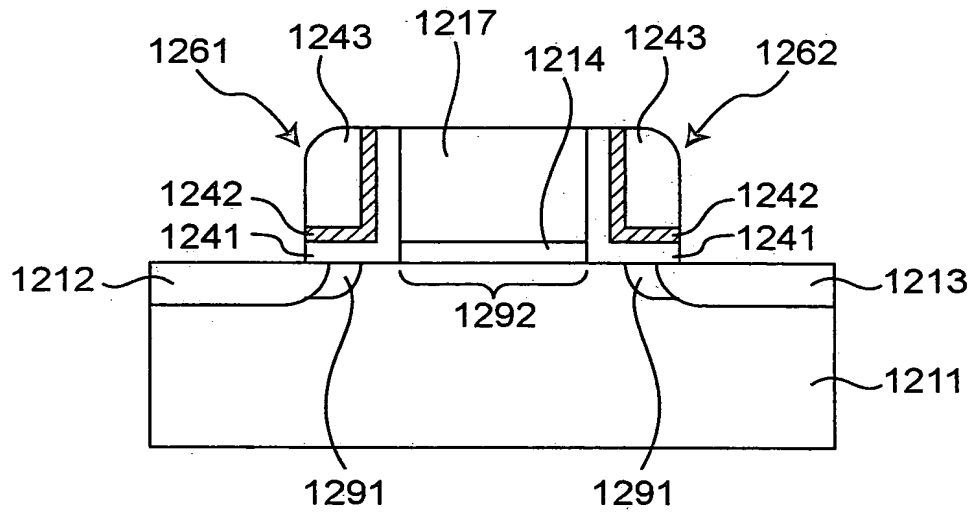
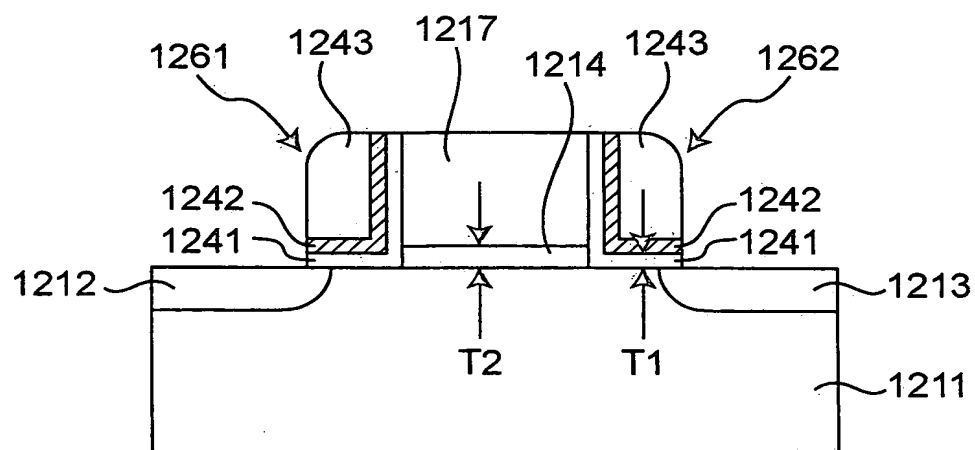


Fig. 17



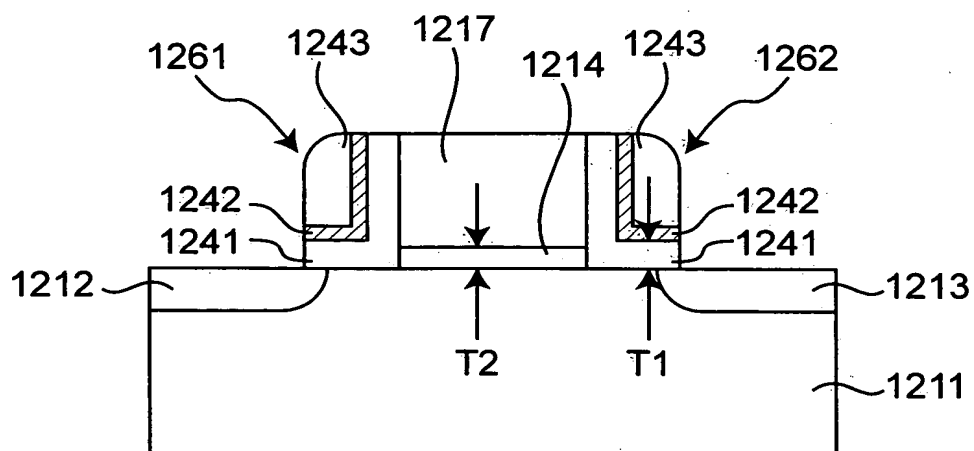
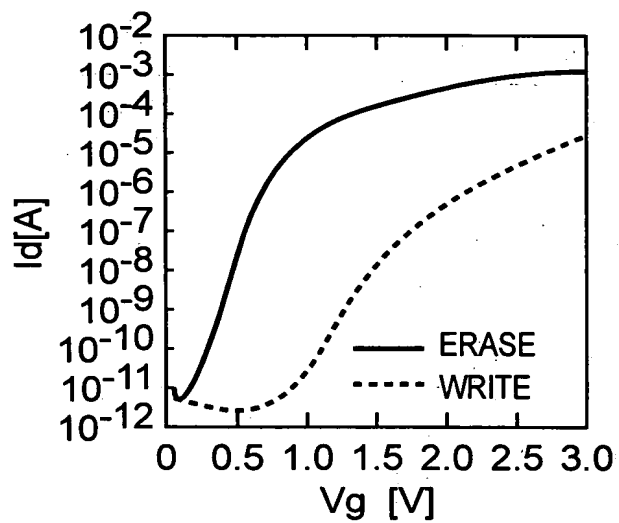
*Fig. 18**Fig. 19*

Fig. 20

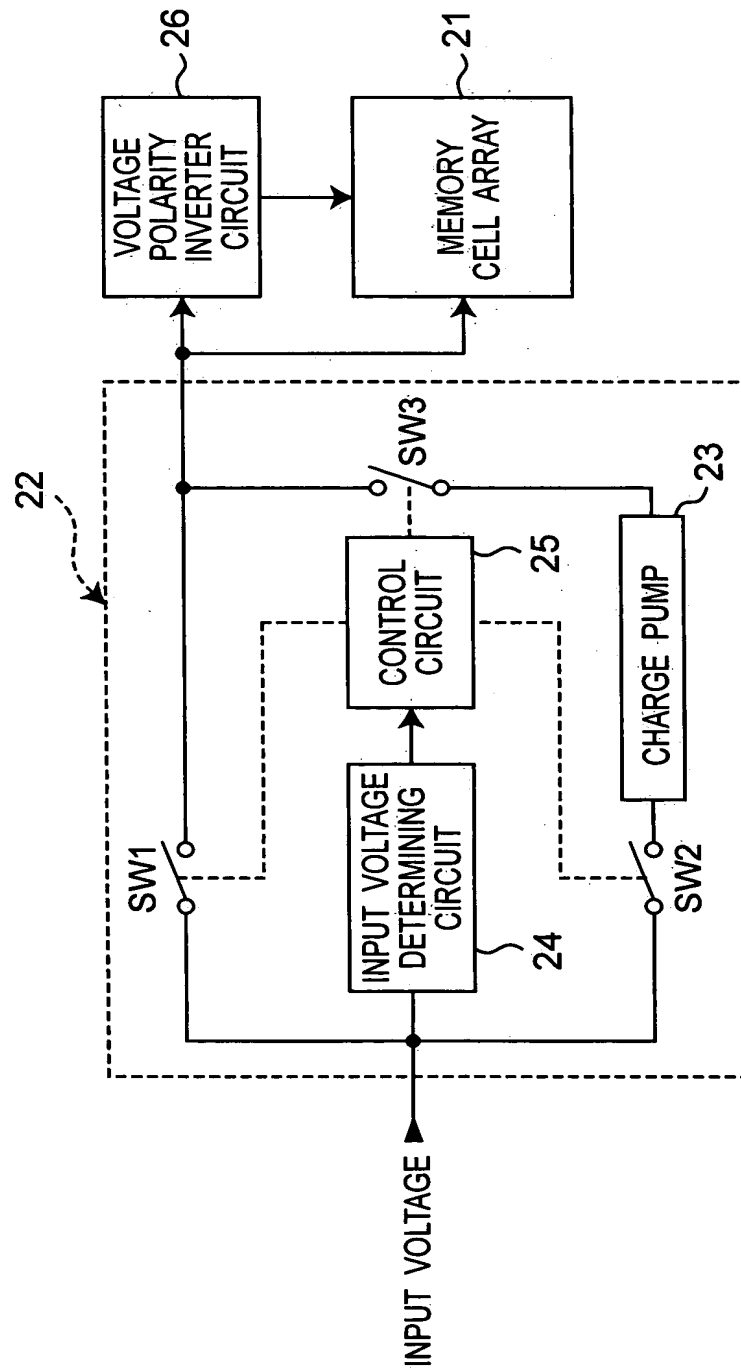


Fig.21

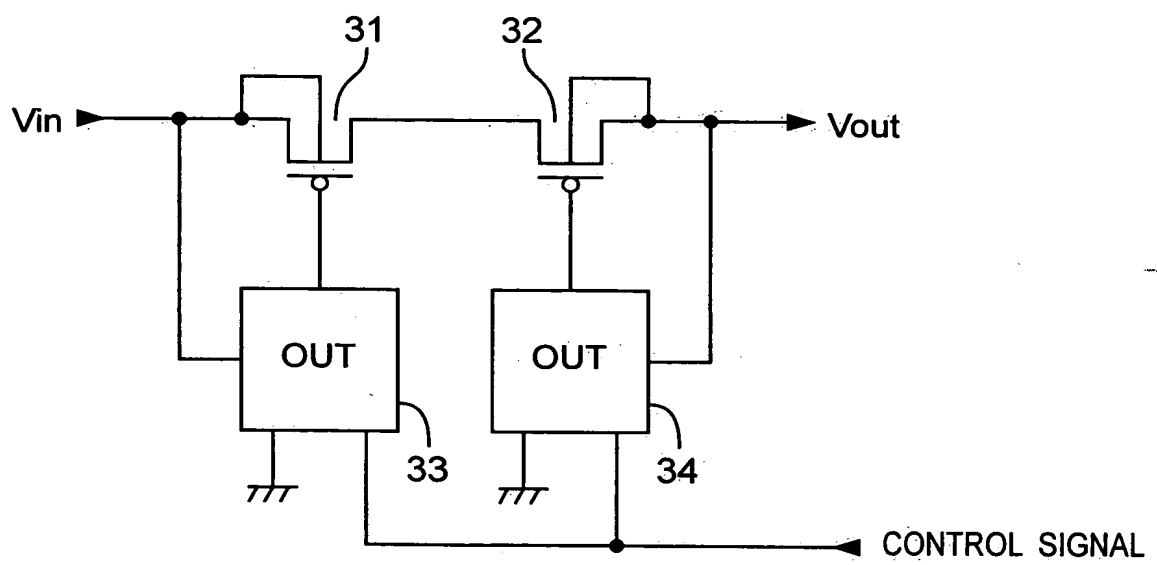
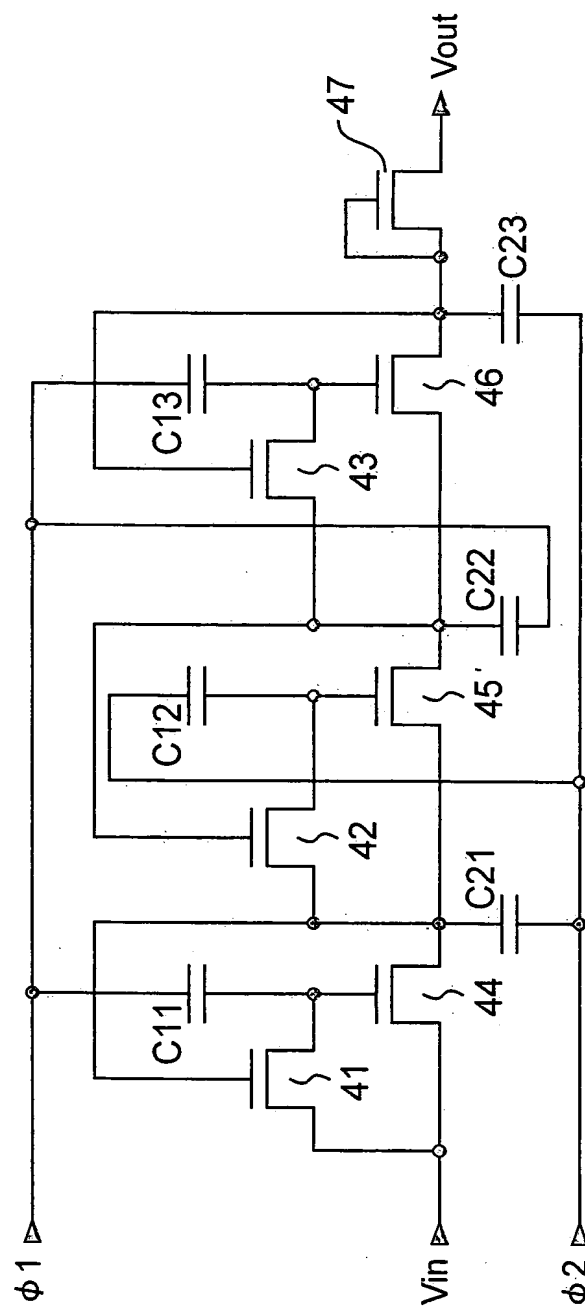


Fig. 22



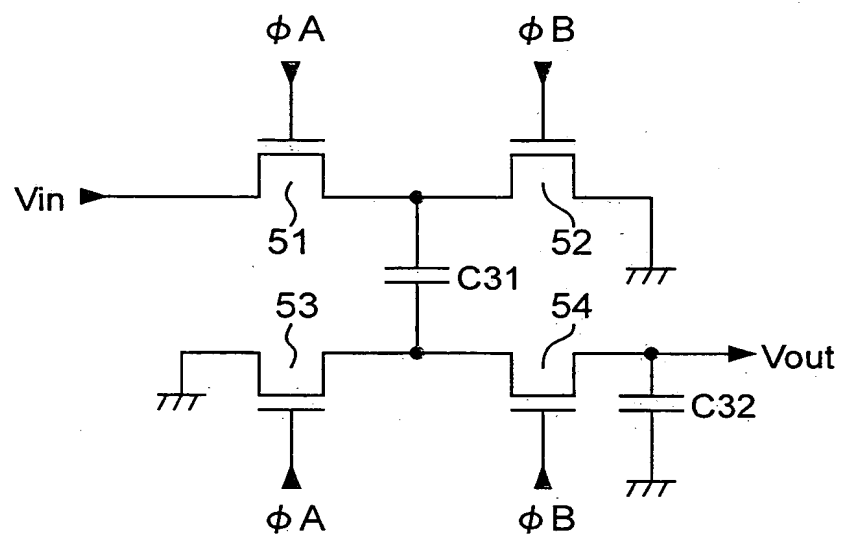
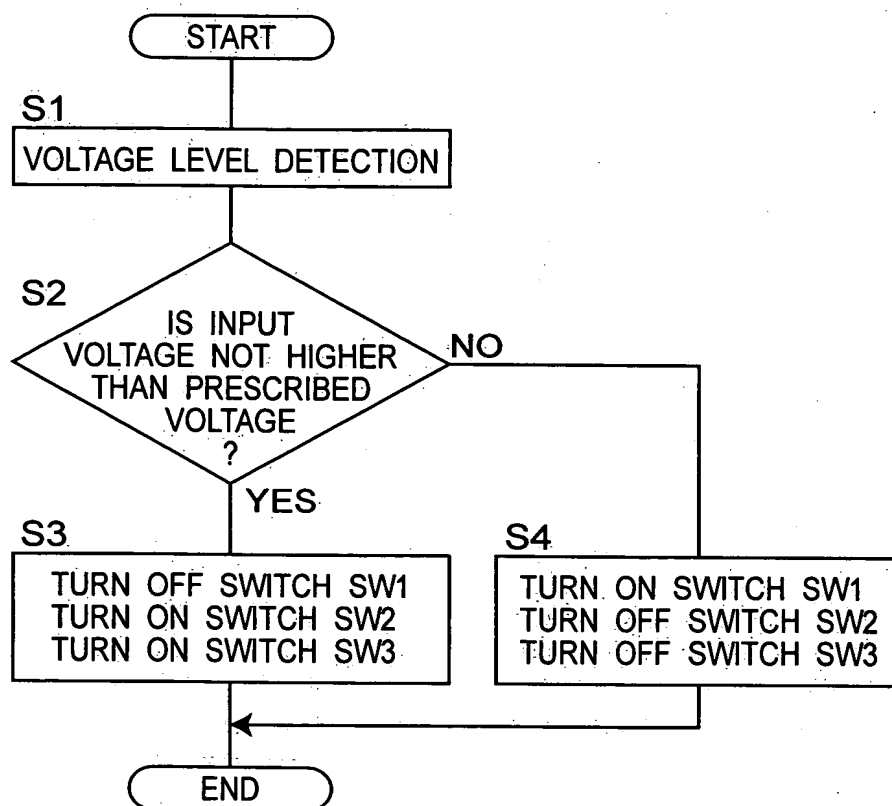
*Fig.23*

Fig.24





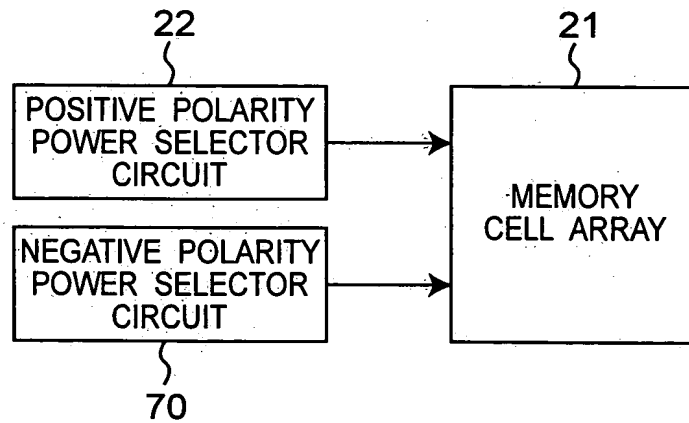
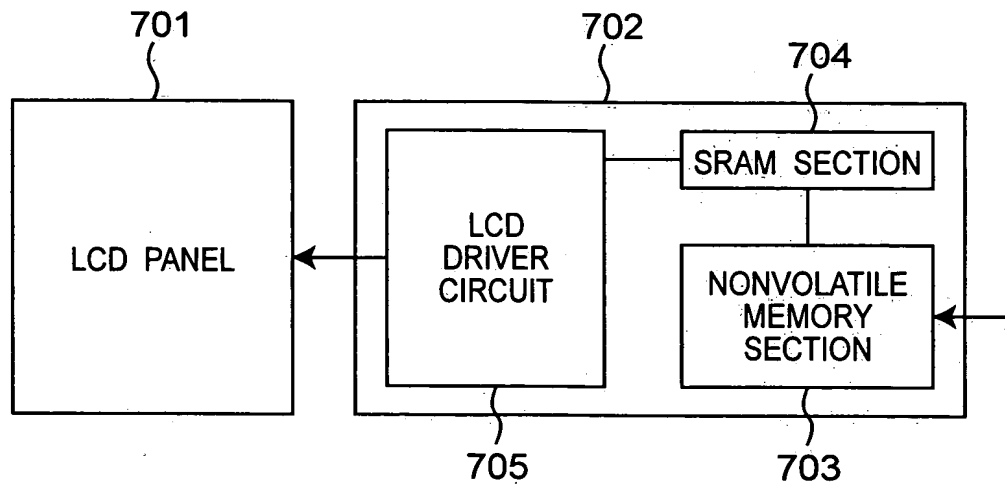
*Fig. 25**Fig. 26*

Fig.27

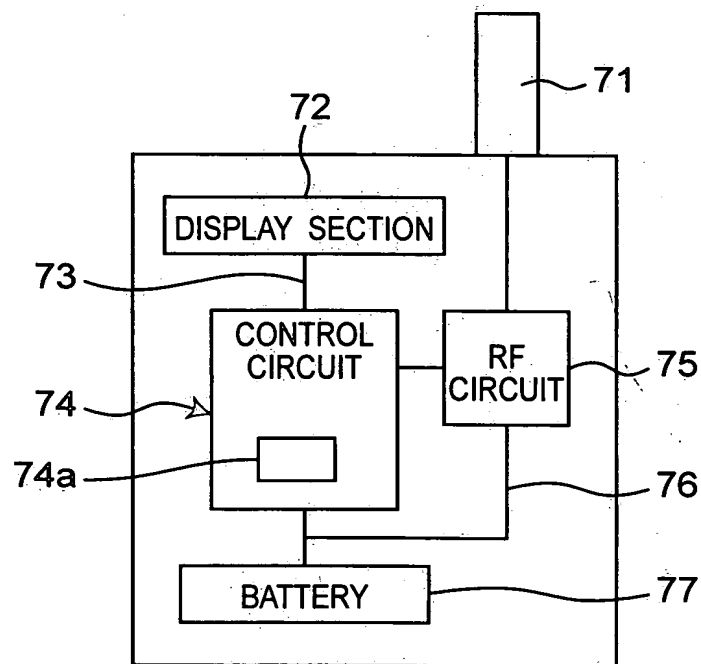


Fig.28

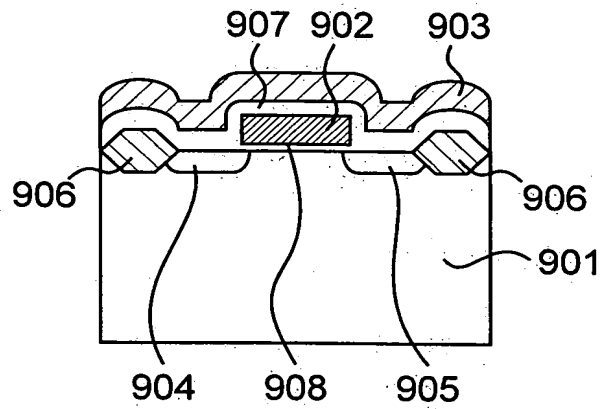


Fig.29

